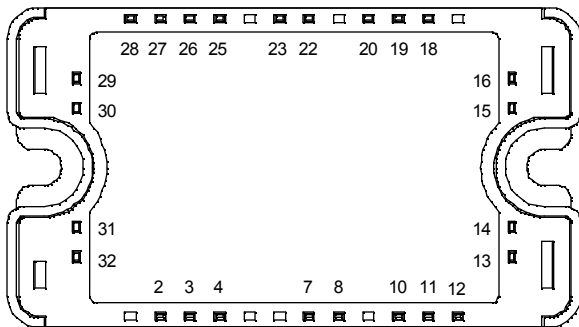
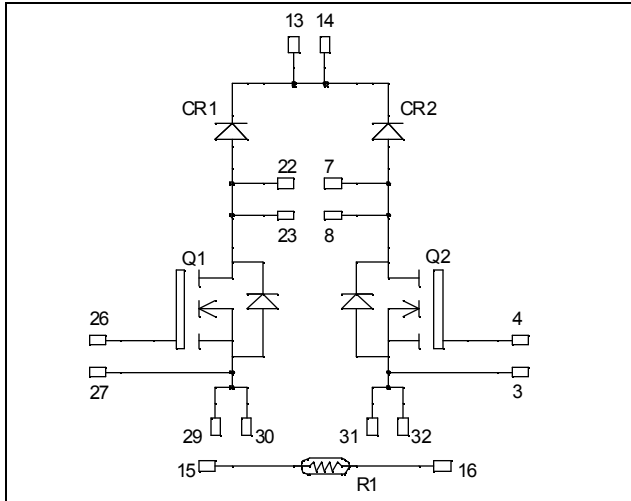


## Dual boost chopper Super Junction MOSFET Power Module

$$V_{DSS} = 600V$$

$$R_{DSon} = 35m\Omega \text{ max @ } T_j = 25^\circ C$$

$$I_D = 72A \text{ @ } T_c = 25^\circ C$$



All multiple inputs and outputs must be shorted together  
 Example: 13/14 ; 29/30 ; 22/23 ...

### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

### Features




- Ultra low  $R_{DSon}$
- Low Miller capacitance
- Ultra low gate charge
- Avalanche energy rated
- Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	600	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	72
		$T_c = 80^\circ C$	54
$I_{DM}$	Pulsed Drain current	288	
$V_{GS}$	Gate - Source Voltage	$\pm 20$	V
$R_{DSon}$	Drain - Source ON Resistance	35	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	416
$I_{AR}$	Avalanche current (repetitive and non repetitive)	20	A
$E_{AR}$	Repetitive Avalanche Energy	1	mJ
$E_{AS}$	Single Pulse Avalanche Energy	1800	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$			40	$\mu\text{A}$
		$T_j = 25^\circ\text{C}$				
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 0V, V_{DS} = 600V$			375	$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$				
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5.4\text{mA}$	2.1	3	3.9	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 150$	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		14		nF
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		5.13		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.42		
$Q_g$	Total gate Charge	$V_{GS} = 10V$		518		nC
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 300V$		58		
$Q_{gd}$	Gate – Drain Charge	$I_D = 72A$		222		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching @ <math>125^\circ\text{C}</math></b>		21		ns
$T_r$	Rise Time	$V_{GS} = 15V$		30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400V$		283		
$T_f$	Fall Time	$I_D = 72A$		84		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b>		1340		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 400V$		1960		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b>		2192		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy	$I_D = 72A, R_G = 2.5\Omega$		2412		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$		350	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		600	
$I_F$	DC Forward Current			80		A
$V_F$	Diode Forward Voltage	$I_F = 80A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$		1.45	V
			$T_j = 125^\circ\text{C}$		1.35	
$t_{rr}$	Reverse Recovery Time	$I_F = 80A$ $V_R = 300V$	$T_j = 25^\circ\text{C}$		95	ns
			$T_j = 125^\circ\text{C}$		115	
$Q_{rr}$	Reverse Recovery Charge	$di/dt = 4500A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		5.2	$\mu\text{C}$
			$T_j = 125^\circ\text{C}$		8	

## Thermal and package characteristics

Symbol Characteristic

		Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	Transistor		0.3	°C/W	
		Diode		0.8		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, I <sub>isol</sub> < 1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

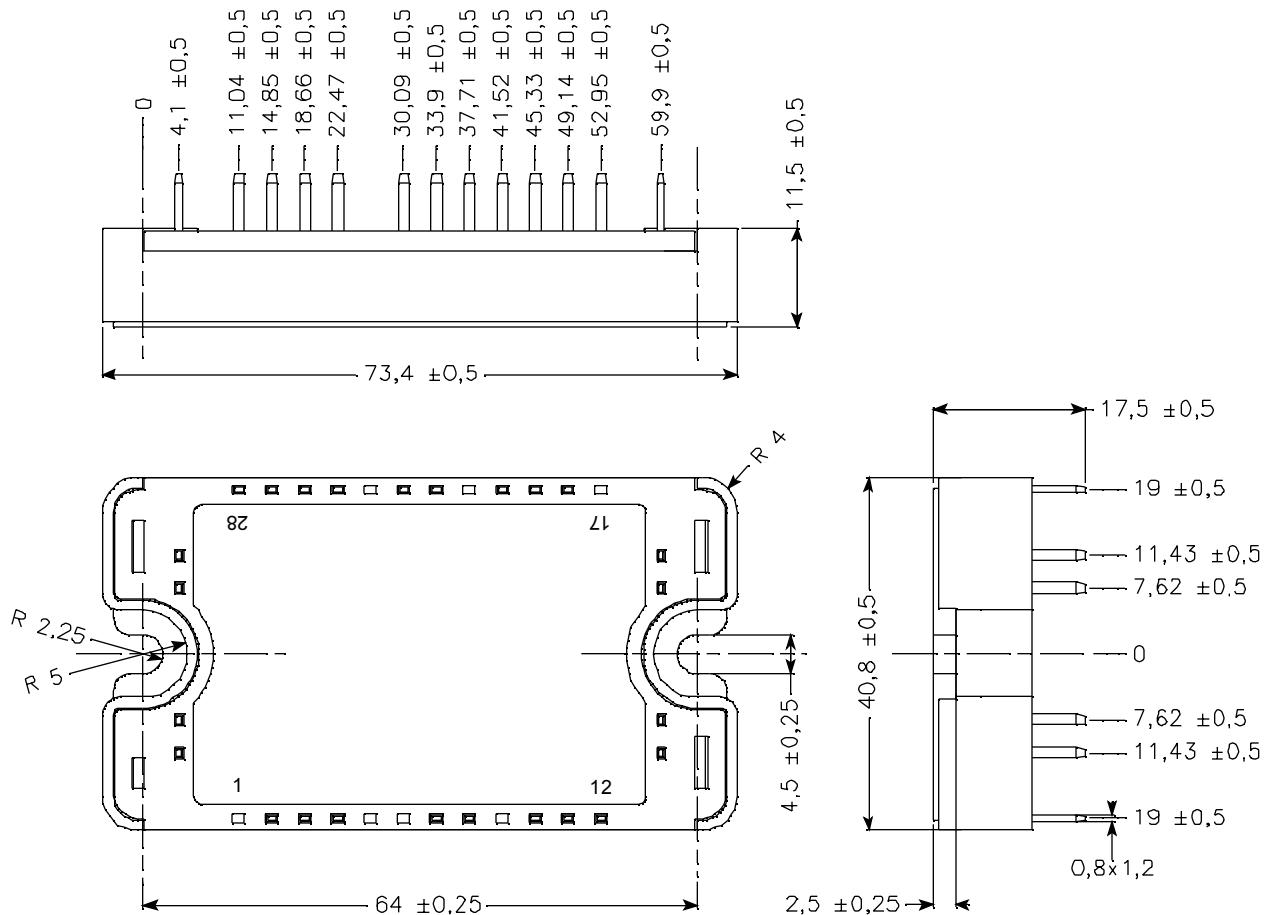
Symbol Characteristic

		Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

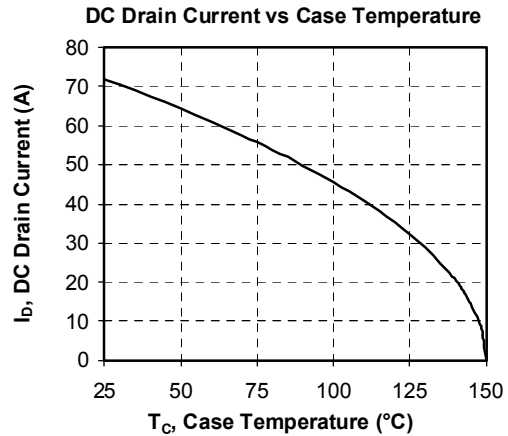
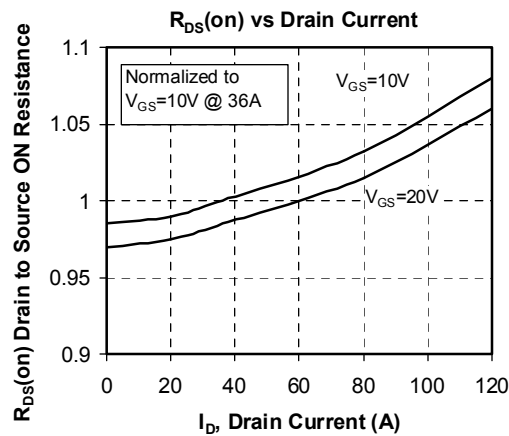
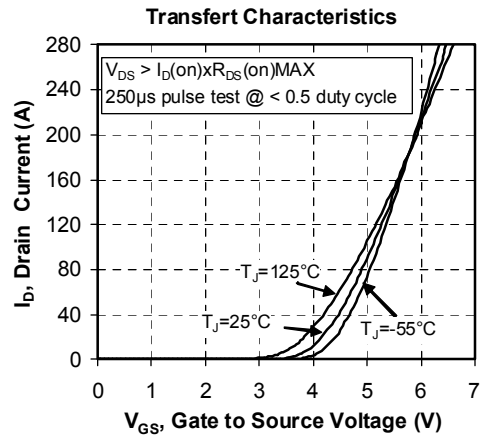
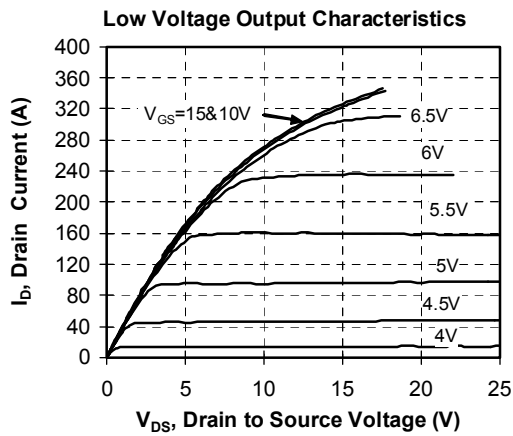
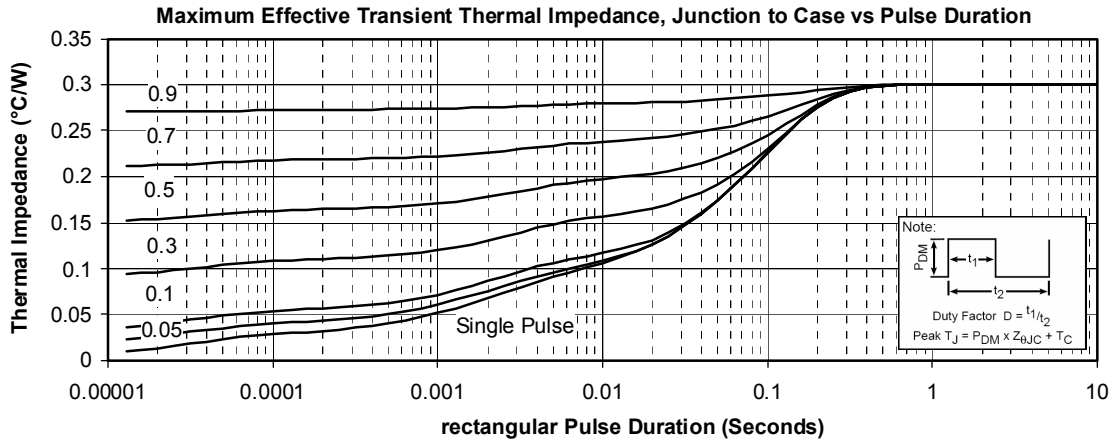
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

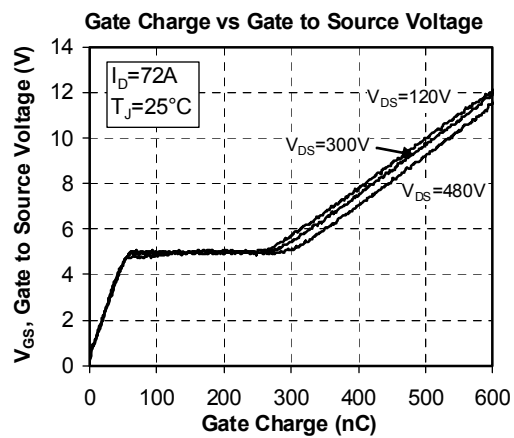
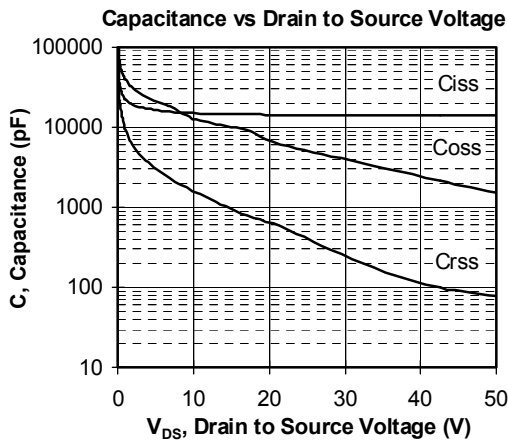
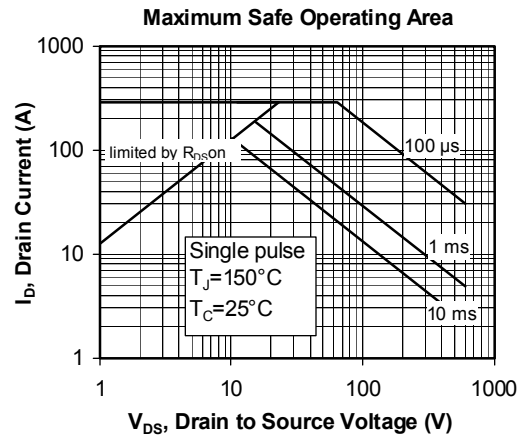
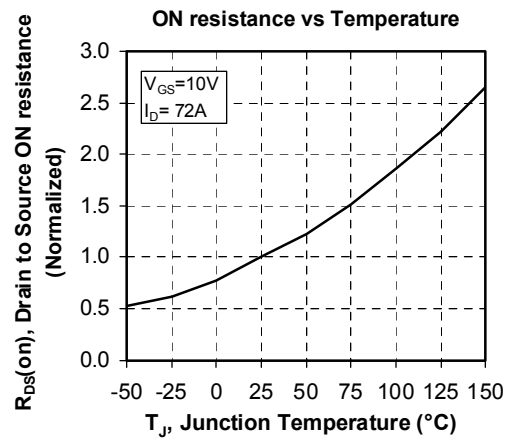
## SP3 Package outline (dimensions in mm)

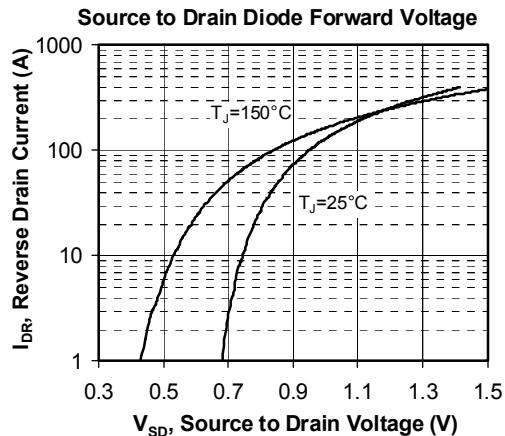
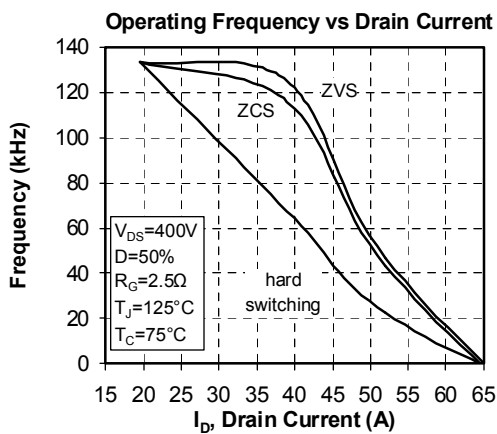
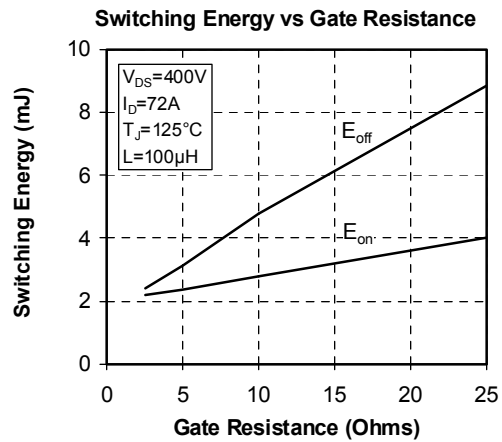
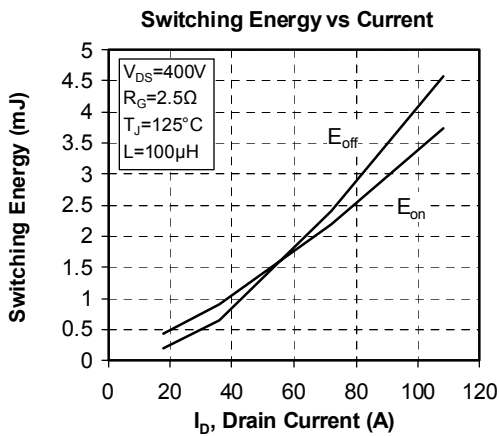
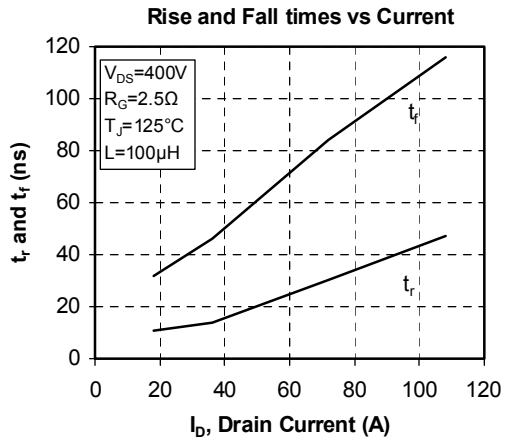
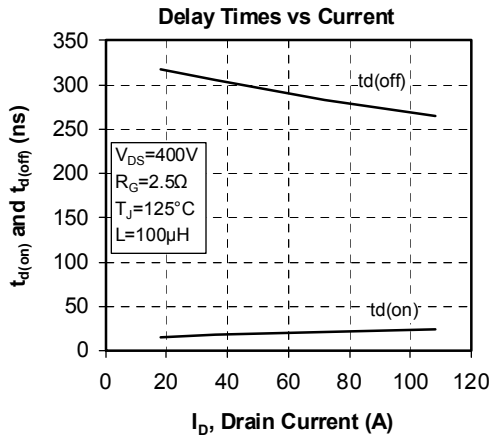


See application note 1901 - Mounting Instructions for SP3 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve







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